



Green Products

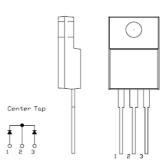
SBRF10100CTL SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

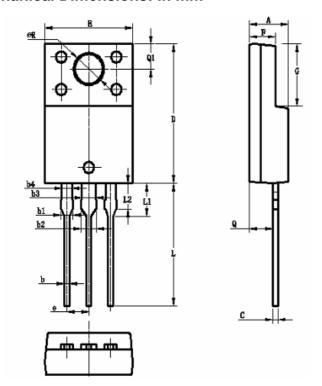
Features:

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



OUTLINE DRAWING

Mechanical Dimensions: In mm



	OPTION 1(CJ)		OPTIO	N 2(HD)
Dim	Min Max		Min	Max
Α	4.4	4.6	4.30	4.70
b	0.6T	ΥP	0.50	0.75
b1	1.3T	ΥP	1.30	1.40
b2	1.7T	ΥP	1.70	1.80
b3	1.6T	ΥP	1.50	1.75
b4	1.2T	ΥP	1.10	1.35
С	0.60	ГҮР	0.50	0.75
D	14.8	15.1	14.80	15.20
Е	10.06	10.26	9.96	10.36
е	2.55	ГҮР	2.54TYP	
F	2.9	3.1	2.80	3.20
G	6.5	6.9	6.50	6.90
L	12.7	13.7	12.8	13.2
L1	3.4	3.8	3.60	4.00
L2	2.6	3.0	-	-
Q	2.5	2.9	2.50	2.90
Q1	2.5 2.9		2.70REF	
ØR	3.5REF		3.50REF	

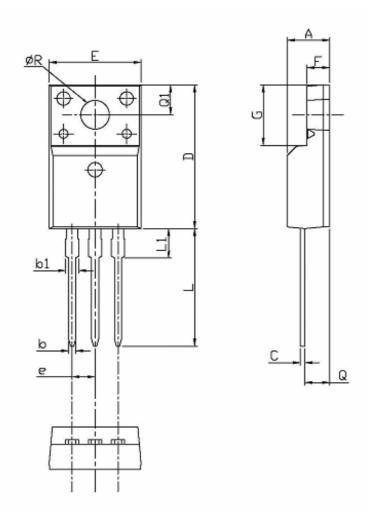
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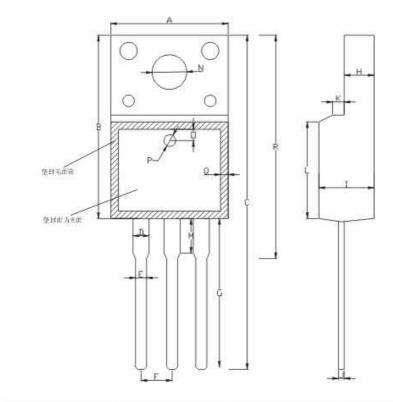
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	OPTION 3		OPTION 4		
Dim	Min	Max	Min	Max	
Α	4.53	4.93	4.50	4.90	
b	0.71	0.91	0.70	0.90	
b1	1.15	1.39	1.33	1.47	
С	0.36	0.53	0.45	0.60	
D	15.67	16.07	15.67	16.07	
E	9.96	10.36	9.96	10.36	
е	2.54TYP		2.54 BSC		
F	2.34	2.76	2.34	2.74	
G	6.50	6.90	6.48	6.88	
L	12.37	12.77	12.78	13.18	
L1	2.23	2.63	3.03	3.43	
Q	2.56	2.96	2.56	2.96	
Q1	3.10	3.50	3.10	3.50	
ØR	2.98	3.38	3.08	3.28	



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A:10.20	± 0.50	B:15.90	± 0.50	C:29.00	± 1.00	D:1.24	± 0.10
E:0.80	± 0.10	F:2.54	± 0.10	G:13.10	$\pm 1,0$	H:2.55	± 0.05
		J:0.50					± 0.50
M:3.00	±0.50	N:3.20	± 0.20	O:1,25	± 0.05	P:1.5	± 0.05
Q:1.0	±0.20	R:19.2	±1.0				

OPTION 5 (SR)

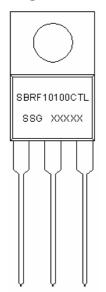
ITO-220AB





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Marking Diagram:



Where XXXXX is YYWWL

SBR = Device Type F = Package type

10 = Forward Current (10A) 100 = Reverse Voltage (100V)

CTL = Configuration

SSG = SSG YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SDDE40400CTI	ITO-220AB	FOrce / tube
SBRF10100CTL	(Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C = 105℃, rectangular wave form	10	А
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	Surge applied at rated load conditions halfwave, single phase,60Hz	120	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 5 A, Pulse, T _C = 25 °C	0.91	V
(per leg) *	V_{F2}	@ 5 A, Pulse, T _C = 125 °C	0.74	V
Max. Reverse Current (per leg) *	I _{R1}	$@V_R = \text{rated } V_R$ $T_C = 25 ^{\circ}C$	1.0	mA
	I _{R2}	$@V_R = \text{rated } V_R$ $T_C = 125 ^{\circ}C$	15.0	mA
Repetitive peak reverse current	IRRM	tp = 2 μs square F= 1 kHz	1	Α
Non-Repetitive Avalanche Energy	Eas	T _J = 25 ° C, I _{AS} = 5 A, L = 1mH	12.5	mJ
Max. Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C$ $f_{SIG} = 1MHz$	250	pF
Typical Series Inductance (per leg)	L_S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

^{*} Pulse Width < 300 μ s, Duty Cycle <2%

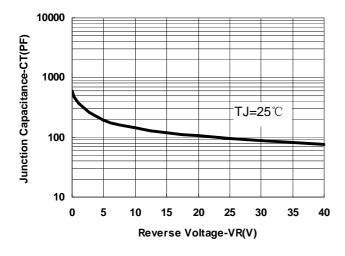
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	°C
Max. Storage Temperature	T_{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	$R_{ ext{ hetaJC}}$	DC operation	3.5	°C/W
Approximate Weight	wt	-	2	g
Case Style		ITO-220AB		

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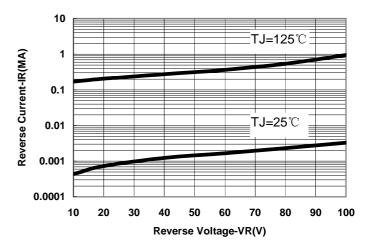


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

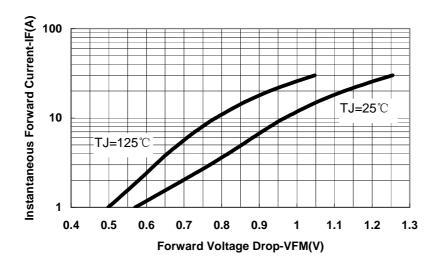


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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SBRF10100CTL

Technical Data Data Sheet N0917, Rev. A **Green Products**

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